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Case No.: 57322US002

TED STATES PATENT AND TRADEMARK OFFICE

First Named Inventor:

BAUDE, PAUL F.

Application No.:

10/076174

Group Art Unit:

1756

Filed:

February 14, 2002

Examiner:

Unknown

Title:

APERTURE MASKS FOR CIRCUIT FABRICATION

Information Disclosure Statement

Commissioner for Patents Washington, DC 20231

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents,

Washington, DC 20231 on:

MAY 2002

Date

Dear Sir:

Pursuant to 37 C.F.R. §§ 1.97 and 1.98, enclosed please find a completed PTO-1449 form citing references submitted for consideration during examination of the above-referenced patent application. A copy of each of the references cited therein is also enclosed.

It is respectfully requested that the Examiner initial and return the enclosed PTO-1449 form in order to indicate that each of the references listed thereon has been considered in connection with the present application.

Respectfully submitted,

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Substi	tute fo	r form 1449A/PTO (modified)	Application Number	10/076174	
2		MATION DICOLOCUDE	Filing Date	February 14, 2002	
		MATION DISCLOSURE	First Named Inventor	Baude, Paul F.	
STATEMENT BY APPLICANT			Art Unit	1756	
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MAY 1 7 2007 Page 2 of 2			Attorney Case Number	57322US002	
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To IR	ADEMAS	OTHER PRIOR ART NON	PATENT LITERATURE DOC	CUMENTS	
Exam. Init.*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published			
	C4	Schon et al., "Fast Organic Electronic C Transistors," Applied Physics Letters, V	Circuits Based on Ambipolar F /ol. 79, No. 24, pp. 4043-404	Pentacene Field-Effect 4 (2001),	
	C5	Gouy et al., "Deposition of Organic Sen Led on Silicon."	niconductor Through Silicon S	Shadow Masks for Integrated	
	C6	Kim et al "Photoplastic Shadow-Mask	s for Rapid Resistless Multi-L	ayer Micropatterning".	

Kim et al., "Dry-Lift-Off Patterning on Fragile Surfaces Using MEMS Shadow Masks," pp. 619-622.

*Examiner:		Date Considered

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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Substitute for form 1449A/PTO (modified)	Application Number	10/076174	
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STATEMENT BY APPLICANT	First Named Inventor	Baude, Paul F.	
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MAY 1 7 2002 Page 1 of 2	Attorney Case Number	57322US002	

Attorney Case Number

57322US002

TRA	DEMARY		U.S. Patent	Documents		
Exam. Cite		Document Number	Publication Date or	Name of Patentee	Pages, Columns, Lines, Where	
Init,*	No.	Doc. Number-(Kind Code if Known)	Issue Date MM-DD-YYYY	or Applicant of Cited Document	Relevant Passages or Relevant Figures Appear	
	A1	US- 3,669,060	06/13/72	Page et al.	A	
	A2	US- 4,096,821	06/27/78	Greeneich et al.	*Ca	
	А3	US- 4,335,161	06/15/82	Luo	MAY	
	A4	US- 4,676,193	06/30/87	Martin	10 2	
	A5	US- 4,746,548	05/24/88	Boudreau et al.	1 100	
	A6	US- 4,915,057	04/10/90	Boudreau et al.	00	
	A7	US- 4,963,921	10/16/90	Kariya et al.	<u> </u>	
	A8	US- 5,397,607	03/14/95	Shields et al.		
	A9	US- 6,087,196	07/11/00	Sturm et al.		
	A10	US- 6,106,627	08/22/00	Yializis		
	A11	US- 6,285,001 B1	09/04/01	Fleming et al.		

			F	oreign Patent	Documents		
Exam.	Cite No.	Foreign Patent Document		Publication Date	Name of Patentee or	Pages, Columns, Lines,	Τ
Init.*		Ctry. Code	Number-KindCode (If known)	MM-DD-YYYY	Applicant of Cited Document	Where Relevant Passages or Relevant Figures Appear	Translation (Check if yes)
	B1	EP	0 118 576	12/02/87			
	B2	EP	0719 638 A2	07/03/96	·		
	В3	JP	5-228669	09/07/93			Х
	B4	JP	9-27454	01/28/97			X
	B5	PCT	WO 99/30336	06/17/99			
	B6	PCT	WO 99/39373	08/05/99			
	В7	PCT	WO 99/54786	10/28/99		· ·	·

		OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS
Exam. Init.*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published
	C1	Brody, "Large Area Masking Techniques for Thin Film Transistor Arrays," SPIE, Vol. 100, Semiconductor Microlithography II, pp. 140-150(1977)
	C2	Weimer, "The TFT- A New Thin-Film Transistor," Proceedings of the IRE, pp. 1462-1469(1962).
	C3	Brody et al., "Flexible Thin-Film Transistors Stretch Performance, Shrink Cost," Research, pp. 20-23 (1969).

*Exam	iner:

Date Considered:

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